## P-Channel 30-V (D-S) MOSFET

These miniature surface mount MOSFETs utilize a high cell density trench process to provide low  $r_{DS(on)}$  and to ensure minimal power loss and heat dissipation. Typical applications are DC-DC converters and power management in portable and battery-powered products such as computers, printers, PCMCIA cards, cellular and cordless telephones.

- Low r<sub>DS(on)</sub> provides higher efficiency and extends battery life
- Low thermal impedance copper leadframe SOIC-8 saves board space
- Fast switching speed
- High performance trench technology

PRODUCT SUMMARY					
V <sub>DS</sub> (V)	$r_{\mathrm{DS(on)}} m(\Omega)$		I <sub>D</sub> (A)		
-30	$19 @ V_{GS} = -10V$	V	-9.5		
	$30 @ V_{GS} = -4.5$	V	-7.5		
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ABSOLUTE MAXIMUM RATINGS ( $T_A = 25$ °C UNLESS OTHERWISE NOTED)						
Parameter			Maximum	Units		
Drain-Source Voltage		$V_{DS}$	-30	V		
Gate-Source Voltage		V <sub>GS</sub>	±25			
Cartineer Drain Commut <sup>a</sup>	$T_A=25^{\circ}C$	I <sub>D</sub>	-9.5			
Continuous Drain Current <sup>a</sup>	$T_{A}=25^{\circ}C$ $T_{A}=70^{\circ}C$		-8.3	А		
Pulsed Drain Current <sup>b</sup>		I <sub>DM</sub>	±50			
Continuous Source Current (Diode Conduction) <sup>a</sup>			-2.1	А		
	$T_A=25^{\circ}C$	PD	3.1	W		
Power Dissipation <sup>a</sup>	$T_{A}=25^{\circ}C$ $T_{A}=70^{\circ}C$	I D	2.6	٧V		
Operating Junction and Storage Temperature Range			-55 to 150	°C		

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THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Maximum	Units		
Maximum Junction-to-Case <sup>a</sup>	t <= 5 sec	$R_{\theta JC}$	25	°C/W		
Maximum Junction-to-Ambient <sup>a</sup>	t <= 10 sec	$R_{\theta JA}$	50	°C/W		

Notes

a. Surface Mounted on 1" x 1" FR4 Board.

b. Pulse width limited by maximum junction temperature

Doworro to v	S-mah - 1	Symbol Test Conditions		Limits		Unit	
Parameter	Symbol			Тур	Max		
Static							
Drain-Source Breakdown Voltage	V(BR)DSS	$V_{GS} = 0 V$ , $I_D = -250 uA$	-30			V	
Gate-Threshold Voltage	VGS(th)	$V_{DS} = V_{GS}, I_D = -250 \text{ uA}$	-1	-1.6	-3	v	
Gate-Body Leakage	Igss	$V_{DS} = 0 V, V_{GS} = \pm 4.5 V$			±200	nA	
Zara Cata Valtaga Drain Current	IDSS	$V_{DS} = -24 V, V_{GS} = 0 V$			-1	uA	
Zero Gate Voltage Drain Current	IDSS	$V_{DS} = -24 V, V_{GS} = 0 V, T_J = 55^{\circ}C$			-5	uA	
On-State Drain Current <sup>A</sup>	ID(on)	$V_{DS} = -5 V, V_{GS} = -10 V$	-50			Α	
		$V_{GS} = -10 \text{ V}, \text{ I}_D = -9.5 \text{ A}$		16	19		
Drain-Source On-Resistance <sup>A</sup>	IDS(on)	$V_{GS} = -4.5 \text{ V}, I_D = -7.5 \text{ A}$		26	30	mΩ	
		$V_{GS} = -10 V$ , $I_D = -9.5 A$ , $T_J = 55^{\circ}C$		20	29		
Forward Tranconductance <sup>A</sup>	g <sub>fs</sub>	$V_{DS} = -15 \text{ V}, \text{ I}_D = -9.5 \text{ A}$		31		S	
Diode Forward Voltage	Vsd	$I_{S} = -2.1 A, V_{GS} = 0 V$		-0.7	-1.2	V	
Dynamic <sup>b</sup>							
Total Gate Charge	Qg	$V_{DS} = -15 V$ , $V_{GS} = -4.5 V$ ,		12.8	20		
Gate-Source Charge	Qgs	$V_{DS} = -15 \text{ v}, \text{ V}_{GS} = -4.5 \text{ v},$ ID = -9.5 A		4.5		nC	
Gate-Drain Charge	Qgd	1D = -9.3  A		5			
Switching	<u> </u>					-	
Turn-On Delay Time	td(on)	$V_{DD} = -15 \text{ V}, R_L = 15 \Omega$ , $I_D = -1 \text{ A},$		15	26	nS	
Rise Time	tr			12	21		
Turn-Off Delay Time	td(off)	$V_{\rm GEN} = -10 \ V, \ R_{\rm G} = 6 \Omega$		62	108	113	
Fall-Time	tf			46	71		

Notes

a. Pulse test:  $PW \le 300$ us duty cycle  $\le 2\%$ .

b. Guaranteed by design, not subject to production testing.

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## Ordering information

## • AM4835EP-T1-XX

- A: Analog Power
- M: MOSFET
- 4835: Part number
- E: ESD Protected
- P: P-Channel
- T1: Tape & reel
- XX: Blank: StandardPF: Leadfree